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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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# **ULTRAFAST SOFT RECOVERY RECTIFIER DIODE**

#### **PRODUCT APPLICATIONS**

- Anti-Parallel Diode
  - -Switchmode Power Supply -Inverters
- Free Wheeling Diode
  - -Motor Controllers
  - -Converters
  - -Inverters
- · Snubber Diode

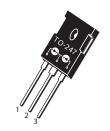
• PFC

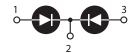
### **PRODUCT FEATURES**

- · Ultrafast Recovery Times
- Soft Recovery Characteristics
- · Popular TO-247 Package
- · Low Forward Voltage
- Low Leakage Current

#### **PRODUCT BENEFITS**

- Low Losses
- · Low Noise Switching
- · Cooler Operation
- · Higher Reliability Systems
- Increased System Power Density





- 1 Anode 1
- 2 Common Cathode Back of Case - Cathode
- 3 Anode 2

#### **MAXIMUM RATINGS**

All Ratings Per Leg: T<sub>C</sub> = 25°C unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT15D40BCT(G)	UNIT
V <sub>R</sub>	Maximum D.C. Reverse Voltage		
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage	400	Volts
V <sub>RWM</sub>	Maximum Working Peak Reverse Voltage		
I <sub>F(AV)</sub>	Maximum Average Forward Current (T <sub>C</sub> = 140°C, Duty Cycle = 0.5)	15	
I <sub>F(RMS)</sub>	RMS Forward Current (Square wave, 50% duty)	36	Amps
I <sub>FSM</sub>	Non-Repetitive Forward Surge Current (T <sub>J</sub> = 45°C, 8.3ms)	110	
T <sub>J</sub> ,T <sub>STG</sub>	Operating and StorageTemperature Range	-55 to 175	°C
T <sub>L</sub>	Lead Temperature for 10 Sec.	300	

#### STATIC ELECTRICAL CHARACTERISTICS

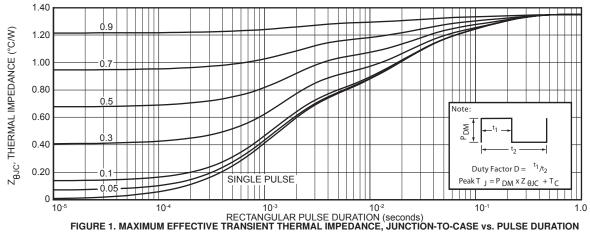
Symbol	Characteristic / Test Conditions		MIN	TYP	MAX	UNIT
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 15A		1.3	1.5	Volts
		I <sub>F</sub> = 30A		1.6		
		I <sub>F</sub> = 15A, T <sub>J</sub> = 125°C		1.2		
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> = V <sub>R</sub> Rated			150	μA
		$V_R = V_R$ Rated, $T_J = 125$ °C			500	
C <sub>T</sub>	Junction Capacitance, V <sub>R</sub> = 200V			33		pF

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t <sub>rr</sub>	Reverse Recovery Time $I_F = 1A$ , $di_F/dt =$	erse Recovery Time $I_F = 1A$ , $di_F/dt = -100A/\mu s$ , $V_R = 30V$ , $T_J = 25^{\circ}C$		19		ns
t <sub>rr</sub>	Reverse Recovery Time	$I_F = 15A$ , $di_F/dt = -200A/\mu s$ $V_R = 266V$ , $T_C = 25^{\circ}C$	-	35		115
Q <sub>rr</sub>	Reverse Recovery Charge		-	60		nC
I <sub>RRM</sub>	Maximum Reverse Recovery Current		-	3	-	Amps
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =15A, di <sub>F</sub> /dt = -200A/µs V <sub>R</sub> = 266V, T <sub>C</sub> = 125°C	-	95		ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	300		nC
I <sub>RRM</sub>	Maximum Reverse Recovery Current		-	6	1	Amps
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 15A, di <sub>F</sub> /dt = -1000A/μs V <sub>R</sub> = 266V, T <sub>C</sub> = 125°C	-	43		ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	540		nC
I <sub>RRM</sub>	Maximum Reverse Recovery Current		-	21		Amps

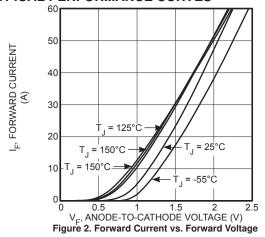
## THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			1.35	°C/W
R <sub>θJA</sub>	Junction-to-Ambient Thermal Resistance			40	
W <sub>T</sub>	Package Weight		0.22		oz
			5.9		g
Torque	Maximum Mounting Torque			10	lb•in
				1.1	N•m

Microsemi Reserves the right to change, without notice, the specifications and information contained herein.



#### **TYPICAL PERFORMANCE CURVES**



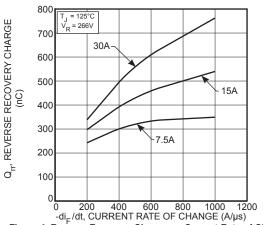
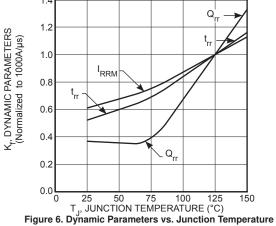
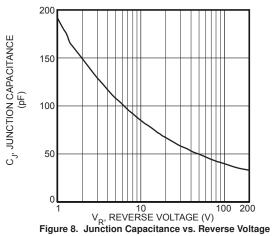


Figure 4. Reverse Recovery Charge vs. Current Rate of Change





## APT15D40BCT(G)

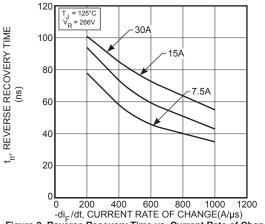


Figure 3. Reverse Recovery Time vs. Current Rate of Change

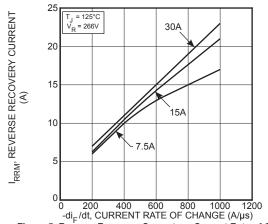


Figure 5. Reverse Recovery Current vs. Current Rate of Change

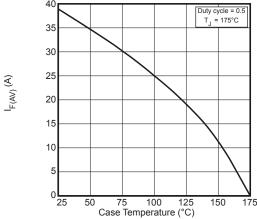


Figure 7. Maximum Average Forward Current vs. CaseTemperature

0.25 I<sub>RR M</sub>

Figure 9. Diode Test Circuit

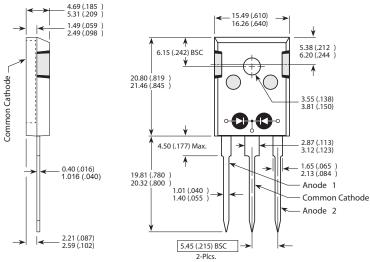
Zero

- 1 I<sub>F</sub> Forward Conduction Current
- 2 di<sub>F</sub>/dt Rate of Diode Current Change Through Zero Crossing.
- 3 I<sub>RRM</sub> Maximum Reverse Recovery Current
- 4 t<sub>rr</sub> Reverse R ecovery Time, measured from zero crossing wher e diode current goes from positive to negative, to the point at which the straight line through I<sub>RRM</sub> and 0.25 P RRM passes through zero .
- 5  $Q_{rr}$  Area Under the Curve Defined by I RRM and  $t_{rr}$ .

Figure 10. Diode Reverse Recovery and Definitions

# TO-247 Package Outline

(e1) SAC: Tin, Silver, Copper



Dimensions in Millimeters and (Inches)